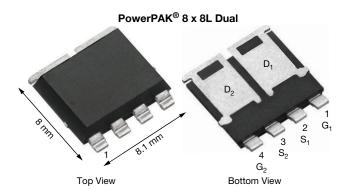
SQJQ900E

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Vishay Siliconix

Automotive Dual N-Channel 40 V (D-S) 175 °C MOSFET



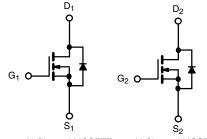
| PRODUCT SUMMARY | |
|---|-----------------|
| V _{DS} (V) | 40 |
| $R_{DS(on)}$ (Ω) at V_{GS} = 10 V | 0.0039 |
| $R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V | 0.0047 |
| I _D (A) per leg | 100 |
| Configuration | Dual |
| Package | PowerPAK 8 x 8L |

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Fully lead (Pb)-free device
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



KONS COMPLIANT HALOGEN



N-Channel MOSFET N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS (| T _C = 25 °C, unles | s otherwise noted | l) | |
|--|--|-----------------------------------|-------------|------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Drain-source voltage | | V _{DS} | 40 | V |
| Gate-source voltage | | V _{GS} | ± 20 | v |
| Continuous drain current | T _C = 25 °C ^a T _C = 125 °C | I- | 100 | |
| Continuous drain current | T _C = 125 °C | I _D | 60 | |
| Continuous source current (diode conduction) ^a | | I _S | 68 | А |
| Pulsed drain current ^b | | I _{DM} | 400 | |
| Single pulse avalanche current | L = 0.1 mH | I _{AS} | 50 | |
| Single pulse avalanche energy | L = 0.1 mm | E _{AS} | 125 | mJ |
| Maximum power dissipation ^b | T _C = 25 °C | | 75 | W |
| Maximum power dissipation ~ | T _C = 125 °C | P _D | 25 | vv |
| Operating junction and storage temperature range | ge | T _J , T _{stg} | -55 to +175 | °C |
| Soldering recommendations (peak temperature) ^{d, e} | | | 260 | C |

| THERMAL RESISTANCE RATINGS | | | | |
|----------------------------|------------------------|-------------------|-------|------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Junction-to-ambient | PCB mount ^c | R _{thJA} | 80 | °C/W |
| Junction-to-case (drain) | | R _{thJC} | 2 | 0/10 |

Notes

a. Package limited

b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

c. When mounted on 1" square PCB (FR4 material)

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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Vishay Siliconix

SQJQ900E

| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
|---|---------------------------|---------------------------|---|------|--------|--------|------|
| Static | | | | • | • | | |
| Drain-source breakdown voltage | V _{DS} | V _{GS} | = 0, I _D = 250 μA | 40 | - | - | v |
| Gate-source threshold voltage | V _{GS(th)} | V _{DS} = | = V _{GS} , I _D = 250 μΑ | 1.5 | 2 | 2.5 | v |
| Gate-source leakage | I _{GSS} | V _{DS} = | $0 \text{ V}, \text{V}_{\text{GS}} = \pm 20 \text{ V}$ | - | - | ± 100 | nA |
| | | $V_{GS} = 0 V$ | V _{DS} = 20 V | - | - | 1 | |
| Zero gate voltage drain current | I _{DSS} | $V_{GS} = 0 V$ | $V_{DS} = 40 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$ | - | - | 50 | μA |
| | | $V_{GS} = 0 V$ | $V_{DS} = 40 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$ | - | - | 150 | |
| On-state drain current ^a | I _{D(on)} | V _{GS} = 10 V | $V_{DS} \ge 5 V$ | 40 | - | - | Α |
| | | V _{GS} = 10 V | I _D = 20 A | - | 0.0034 | 0.0039 | |
| Drain actures an state registeres a | Р | $V_{GS} = 4.5 V$ | I _D = 10 A | - | 0.0039 | 0.0047 | |
| Drain-source on-state resistance ^a | R _{DS(on)} | V _{GS} = 10 V | I _D = 20 A, T _J = 125 °C | - | - | 0.0074 | Ω |
| | | V _{GS} = 10 V | I _D = 20 A, T _J = 175 °C | - | - | 0.0091 | |
| Forward transconductance b | | V _{DS} | = 15 V, I _D = 15 A | - | 105 | - | S |
| Dynamic ^b | | - | | | - | | |
| Input capacitance | C _{iss} | | | - | 4695 | 5900 | |
| Output capacitance | C _{oss} | $V_{GS} = 0 V$ | V_{DS} = 20 V, f = 1 MHz | - | 637 | 800 | pF |
| Reverse transfer capacitance | C _{rss} | | | - | 259 | 330 | |
| Total gate charge ^c | Qg | | | - | 85 | 120 | |
| Gate-source charge ^c | Q _{gs} | $V_{GS} = 10 \text{ V}$ | $V_{DS} = 20 \text{ V}, I_D = 40 \text{ A}$ | - | 10 | - | nC |
| Gate-drain charge ^c | Q _{gd} | | | - | 12 | - | |
| Gate resistance | Rg | | f = 1 MHz | 0.7 | 1.5 | 3.0 | Ω |
| Turn-on delay time ^c | t _{d(on)} | | | - | 14 | 30 | |
| Rise time ^c | t _r | V _{DD} = | = 20 V, R _L = 0.5 Ω | - | 7.5 | 15 | |
| Turn-off delay time ^c | t _{d(off)} | $I_D \cong 40 \text{ A},$ | $V_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$ | - | 30 | 60 | ns |
| Fall time ^c | t _f | | | - | 14 | 30 | |
| Source-Drain Diode Ratings and Cha | racteristics ^b | | | | | | |
| Pulsed current ^a | I _{SM} | | | - | - | 200 | Α |
| Forward voltage | V _{SD} | IF | = 40 A, V _{GS} = 0 | - | 1 | 1.2 | V |
| | | | | | | | |

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

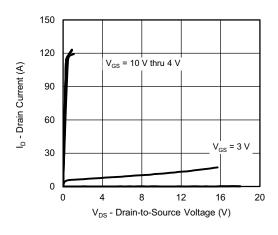
b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

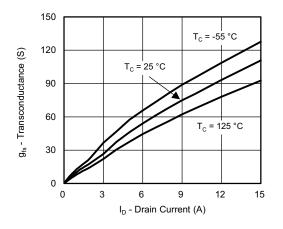
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



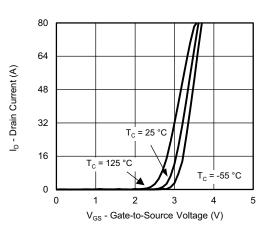
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



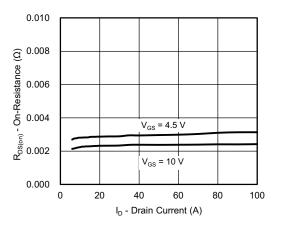
Output Characteristics



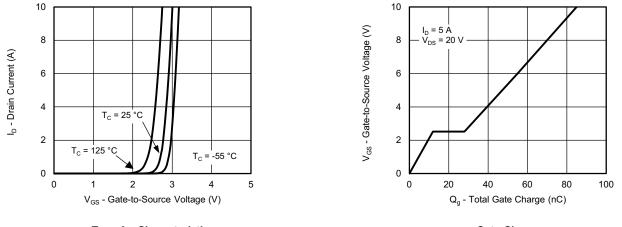
Transconductance



Transfer Characteristics



On-Resistance vs. Drain Current



Transfer Characteristics



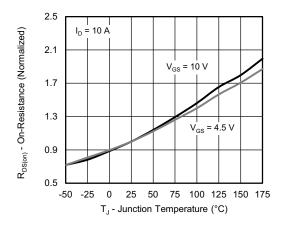
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3 tions. contact: automostechsur Document Number: 62796

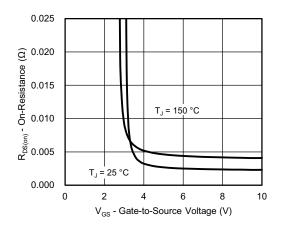
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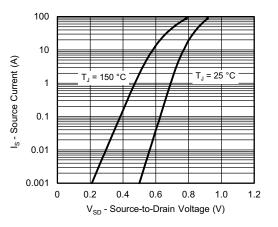
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



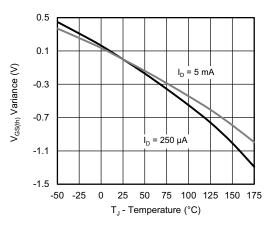
On-Resistance vs. Junction Temperature

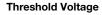


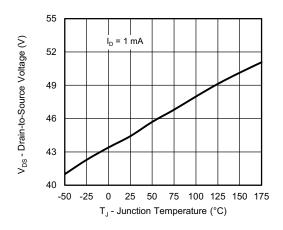
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage







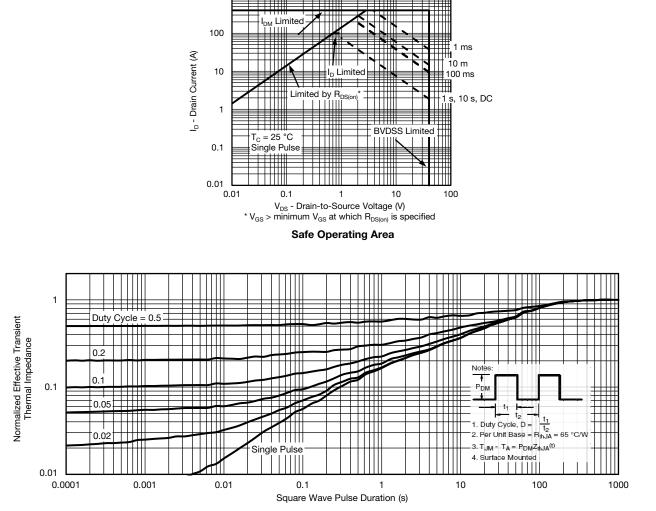
Drain Source Breakdown vs. Junction Temperature

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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)

1000

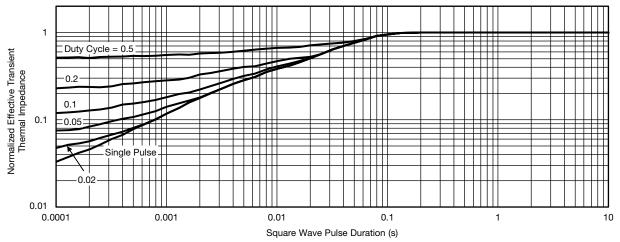


Normalized Thermal Transient Impedance, Junction-to-Ambient



Document Number: 62796

THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)





Note

• The characteristics shown in the two graphs

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- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)

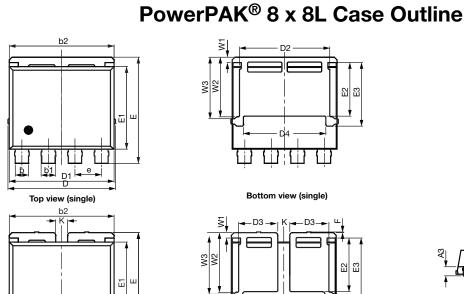
- Normalized Transient Thermal Impedance Junction to Case (25 °C)

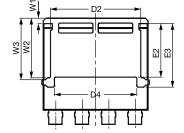
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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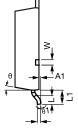
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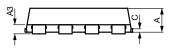




Bottom view (single)



0.25 gauge line





¥, D3 🗕 _D3 W3 W2 Ш

Bottom view (dual)

| DIM. | | MILLIMETERS | | | INCHES | |
|--------------------------|-----------|-------------|------|-------|--------|-------|
| DIM. | MIN. | MIN. NOM. | | MIN. | NOM. | MAX. |
| А | 1.70 | 1.80 | 1.90 | 0.067 | 0.071 | 0.075 |
| A1 | 0.00 | 0.08 | 0.13 | 0.000 | 0.003 | 0.005 |
| A3 | 0.55 | 0.62 | 0.70 | 0.022 | 0.024 | 0.028 |
| b | 0.92 | 1.00 | 1.08 | 0.036 | 0.039 | 0.043 |
| b1 | 1.02 | 1.10 | 1.18 | 0.040 | 0.043 | 0.046 |
| b2 | 7.80 | 7.90 | 8.00 | 0.307 | 0.311 | 0.315 |
| С | 0.20 | 0.25 | 0.30 | 0.008 | 0.010 | 0.012 |
| D | 8.00 | 8.10 | 8.25 | 0.315 | 0.319 | 0.325 |
| D1 | 7.80 | 7.90 | 8.00 | 0.307 | 0.311 | 0.315 |
| D2 | 6.70 | 6.80 | 6.90 | 0.264 | 0.268 | 0.272 |
| D3 | 2.85 | 2.95 | 3.05 | 0.112 | 0.116 | 0.120 |
| D4 | 6.11 | 6.21 | 6.31 | 0.241 | 0.244 | 0.248 |
| е | 1.95 | 2.00 | 2.05 | 0.077 | 0.079 | 0.081 |
| E | 7.90 | 8.00 | 8.10 | 0.311 | 0.315 | 0.319 |
| E1 | 6.12 | 6.22 | 6.32 | 0.241 | 0.245 | 0.249 |
| E2 | 3.94 | 4.04 | 4.14 | 0.140 | 0.159 | 0.163 |
| E3 | 4.69 | 4.79 | 4.89 | 0.185 | 0.189 | 0.193 |
| F | 0.05 | 0.10 | 0.15 | 0.002 | 0.004 | 0.006 |
| L | 0.62 | 0.72 | 0.82 | 0.024 | 0.028 | 0.032 |
| L1 | 0.92 | 1.07 | 1.22 | 0.036 | 0.042 | 0.048 |
| К | 0.80 | 0.90 | 1.00 | 0.031 | 0.035 | 0.039 |
| W | 0.30 | 0.40 | 0.50 | 0.012 | 0.016 | 0.020 |
| W1 | 0.30 | 0.40 | 0.50 | 0.012 | 0.016 | 0.020 |
| W2 | 4.39 | 4.49 | 4.59 | 0.173 | 0.177 | 0.181 |
| W3 | 4.54 | 4.64 | 4.74 | 0.179 | 0.183 | 0.187 |
| θ | 6° | 10° | 14° | 6° | 10° | 14° |
| θ1 | 0° | 3° | 8° | 0° | 3° | 8° |
| -0891-Rev. A, G: 6026 | 06-Oct-14 | | | | | |

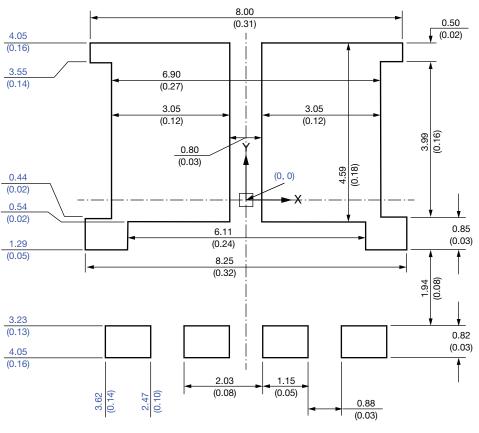
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Recommended Minimum PADs for PowerPAK® 8 x 8L Dual



Dimensions in millimeters (inches)

Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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